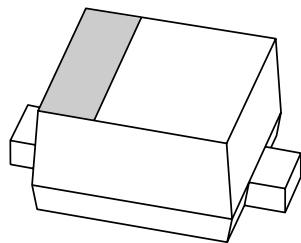


# DATA SHEET



## **BAP65-01** Silicon PIN diode

Preliminary specification

2001 Nov 01

# Silicon PIN diode

# BAP65-01

### FEATURES

- High voltage, current controlled
- RF resistor for RF switches
- Low diode capacitance
- Low diode forward resistance (low loss)
- Very low series inductance.

### APPLICATIONS

- RF attenuators and switches
- Bandswitch for TV tuners
- Series diode for mobile communication transmit/receive switch.

### DESCRIPTION

Planar PIN diode in a SOD723A ultra small SMD plastic package.

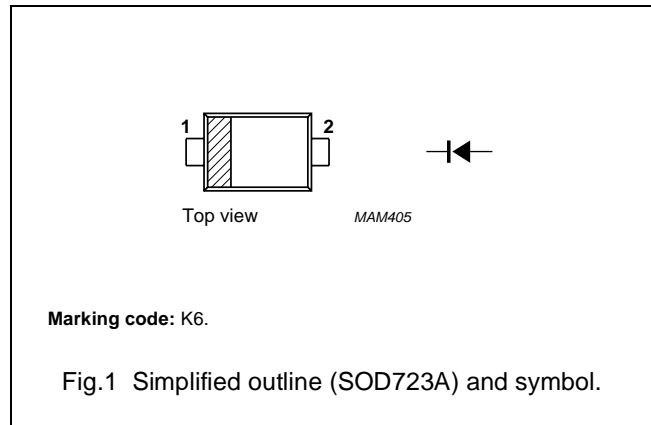
### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_R$	continuous reverse voltage		–	30	V
$I_F$	continuous forward current		–	100	mA
$P_{tot}$	total power dissipation	$T_s \leq 90\text{ }^\circ\text{C}$	–	315	mW
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$
$T_j$	junction temperature		–65	+150	$^\circ\text{C}$

### PINNING

PIN	DESCRIPTION
1	cathode
2	anode



## Silicon PIN diode

## BAP65-01

**ELECTRICAL CHARACTERISTICS** $T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_F$	forward voltage	$I_F = 50\text{ mA}$	0.9	1.1	V
$I_R$	reverse leakage current	$V_R = 20\text{ V}$	–	20	nA
$C_d$	diode capacitance	$V_R = 0\text{ V}; f = 1\text{ MHz}$	0.61	–	pF
		$V_R = 1\text{ V}; f = 1\text{ MHz}$	0.48	0.9	pF
		$V_R = 3\text{ V}; f = 1\text{ MHz}$	0.43	0.8	pF
		$V_R = 20\text{ V}; f = 1\text{ MHz}$	0.375	–	pF
$r_D$	diode forward resistance	$I_F = 1\text{ mA}; f = 100\text{ MHz}$	1.0	–	$\Omega$
		$I_F = 5\text{ mA}; f = 100\text{ MHz}; \text{note 1}$	0.6	0.95	$\Omega$
		$I_F = 10\text{ mA}; f = 100\text{ MHz}; \text{note 1}$	0.5	0.9	$\Omega$
		$I_F = 100\text{ mA}; f = 100\text{ MHz}$	0.3	–	$\Omega$
$ S_{21} ^2$	isolation	$V_R = 0; f = 900\text{ MHz}$	9.4	–	dB
		$V_R = 0; f = 1800\text{ MHz}$	5.5	–	dB
		$V_R = 0; f = 2450\text{ MHz}$	4.1	–	dB
$ S_{21} ^2$	insertion loss	$I_F = 1\text{ mA}; f = 900\text{ MHz}$	0.10	–	dB
		$I_F = 1\text{ mA}; f = 1800\text{ MHz}$	0.12	–	dB
		$I_F = 1\text{ mA}; f = 2450\text{ MHz}$	0.15	–	dB
$ S_{21} ^2$	insertion loss	$I_F = 5\text{ mA}; f = 900\text{ MHz}$	0.08	–	dB
		$I_F = 5\text{ mA}; f = 1800\text{ MHz}$	0.10	–	dB
		$I_F = 5\text{ mA}; f = 2450\text{ MHz}$	0.12	–	dB
$ S_{21} ^2$	insertion loss	$I_F = 10\text{ mA}; f = 900\text{ MHz}$	0.06	–	dB
		$I_F = 10\text{ mA}; f = 1800\text{ MHz}$	0.09	–	dB
		$I_F = 10\text{ mA}; f = 2450\text{ MHz}$	0.11	–	dB
$ S_{21} ^2$	insertion loss	$I_F = 100\text{ mA}; f = 900\text{ MHz}$	0.05	–	dB
		$I_F = 100\text{ mA}; f = 1800\text{ MHz}$	0.08	–	dB
		$I_F = 100\text{ mA}; f = 2450\text{ MHz}$	0.10	–	dB
$\tau_L$	charge carrier life time	when switched from $I_F = 10\text{ mA}$ to $I_R = 6\text{ mA}; R_L = 100\ \Omega$ ; measured at $I_R = 3\text{ mA}$	0.17	–	$\mu\text{s}$
$L_S$	series inductance	$I_F = 100\text{ mA}; f = 100\text{ MHz}$	0.6	–	nH

**Note**

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

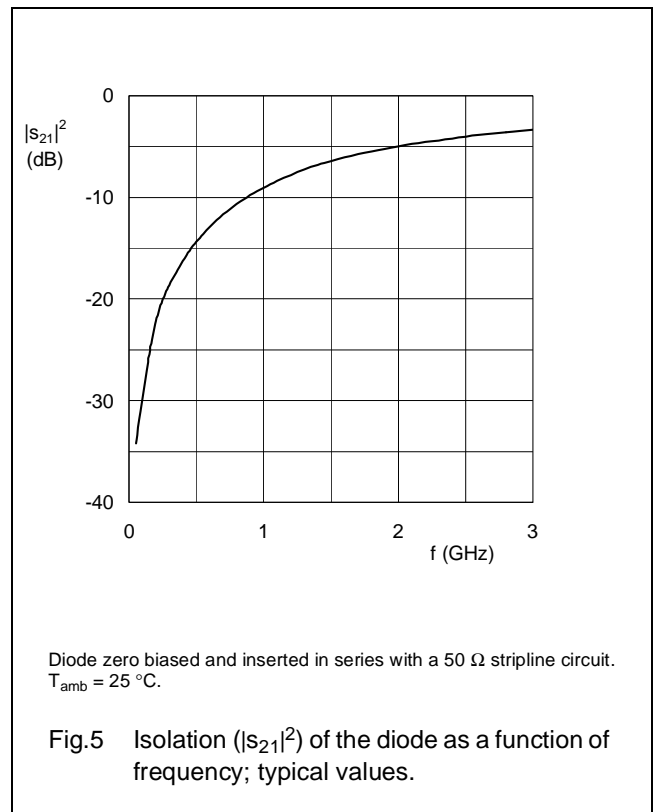
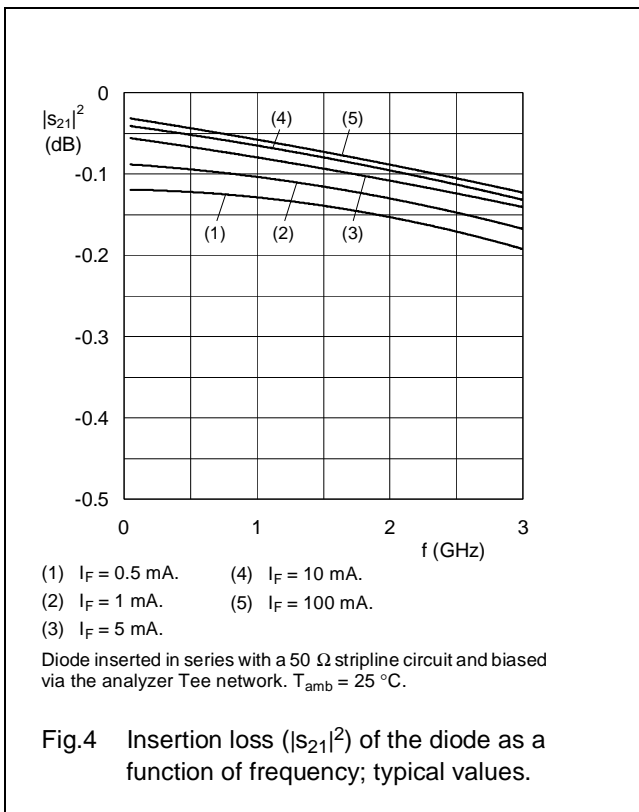
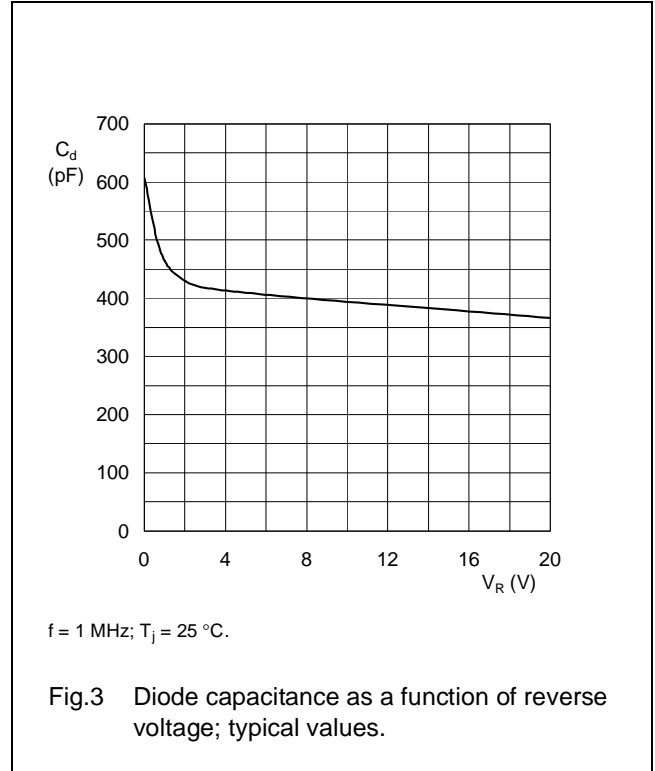
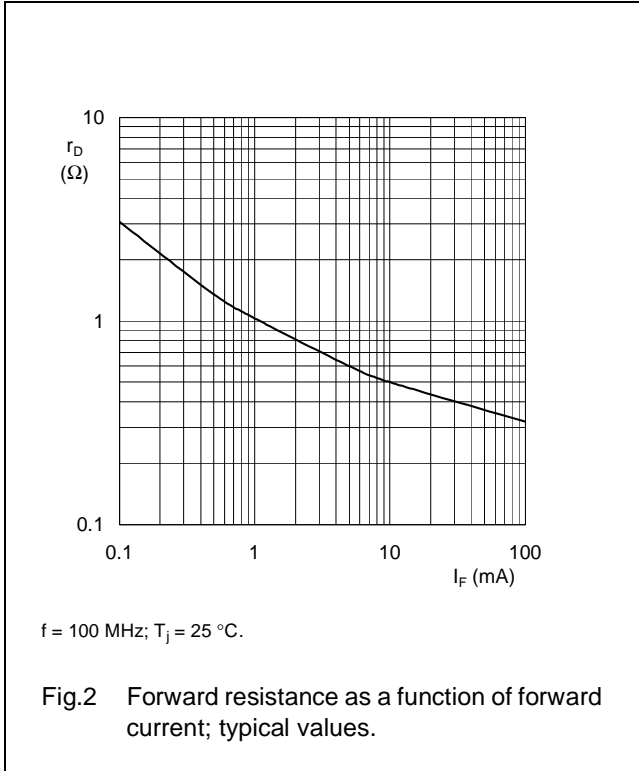
**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	190	K/W

Silicon PIN diode

BAP65-01

GRAPHICAL DATA



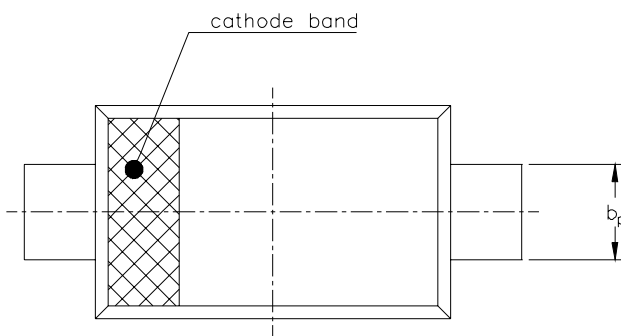
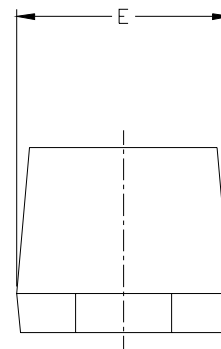
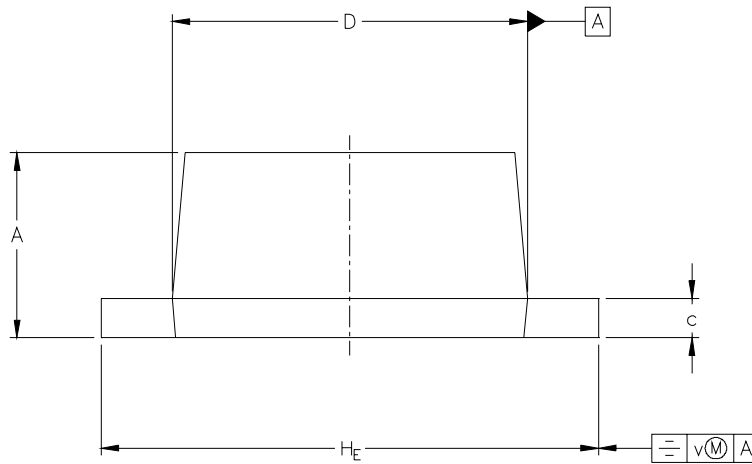
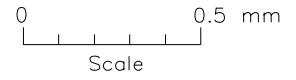
Silicon PIN diode

BAP65-01

PACKAGE OUTLINE

SOD723A

Plastic surface mounted package; 2 leads



UNIT	A	b <sub>p</sub>	c	D	E	H <sub>E</sub>	v
mm	0.49 0.55	0.25 0.32	0.08 0.15	0.95 1.05	0.55 0.65	1.35 1.45	0.1

PACKAGE OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOD723A PUBLICATION DRAWING					01-09-06

UNDER DEVELOPMENT

## Silicon PIN diode

BAP65-01

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DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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